

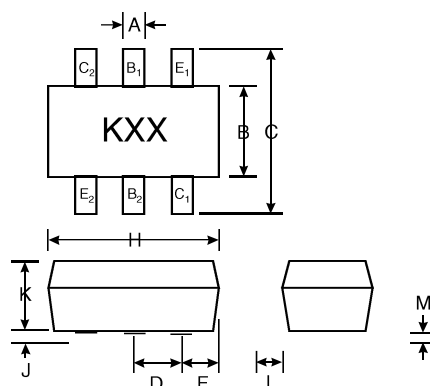


Features

Epitaxial Planar Die Construction
Ideal for Low Power Amplification and Switching
Ultra-Small Surface Mount Package

Mechanical Data

Case: SOT-363, Molded Plastic
Terminals: Solderable per MIL-STD-202, Method 208
Terminal Connections: See Diagram
Marking: K3N
Weight: 0.006 grams (approx.)



SOT-363		
Dim	Min	Max
A	0.10	0.30
B	1.15	1.35
C	2.00	2.20
D	0.65 Nominal	
F	0.30	0.40
H	1.80	2.20
J		0.10
K	0.90	1.00
L	0.25	0.40
M	0.10	0.25
All Dimensions in mm		

Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	MMDT3906	Unit
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-40	V
Emitter-Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous (Note 1)	I_C	-200	mA
Power Dissipation (Note 1)	P_d	200	mW
Thermal Resistance, Junction to Ambient (Note 1)	R_{JA}	625	K/W

- Notes:
1. Valid provided that terminals are kept at ambient temperature.
 2. Pulse test: Pulse width 300 μ s, duty cycle 2%.

Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 2)					
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-40		V	$I_C = -10\text{ A}$, $I_E = 0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-40		V	$I_C = -1.0\text{mA}$, $I_B = 0$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5.0		V	$I_E = -10\text{ A}$, $I_C = 0$
Collector Cutoff Current	I_{CEX}		-50	nA	$V_{CE} = -30\text{V}$, $V_{EB(OFF)} = -3.0\text{V}$
Base Cutoff Current	I_{BL}		-50	nA	$V_{CE} = -30\text{V}$, $V_{EB(OFF)} = -3.0\text{V}$
ON CHARACTERISTICS (Note 2)					
DC Current Gain	h_{FE}	60 80 100 60 30	300		$I_C = -100\mu\text{A}$, $V_{CE} = -1.0\text{V}$ $I_C = -1.0\text{mA}$, $V_{CE} = -1.0\text{V}$ $I_C = -10\text{mA}$, $V_{CE} = -1.0\text{V}$ $I_C = -50\text{mA}$, $V_{CE} = -1.0\text{V}$ $I_C = -100\text{mA}$, $V_{CE} = -1.0\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$		-0.25 -0.40	V	$I_C = -10\text{mA}$, $I_B = -1.0\text{mA}$ $I_C = -50\text{mA}$, $I_B = -5.0\text{mA}$
Base- Emitter Saturation Voltage	$V_{BE(SAT)}$	-0.65	-0.85 -0.95	V	$I_C = -10\text{mA}$, $I_B = -1.0\text{mA}$ $I_C = -50\text{mA}$, $I_B = -5.0\text{mA}$
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C_{obo}		4.5	pF	$V_{CB} = -5.0\text{V}$, $f = 1.0\text{MHz}$, $I_E = 0$
Input Capacitance	C_{ibo}		10	pF	$V_{EB} = -0.5\text{V}$, $f = 1.0\text{MHz}$, $I_C = 0$
Input Impedance	h_{ie}	2.0	12	k	$V_{CE} = 10\text{V}$, $I_C = 1.0\text{mA}$, $f = 1.0\text{kHz}$
Voltage Feedback Ratio	h_{re}	0.1	10	$\times 10^{-4}$	
Small Signal Current Gain	h_{fe}	100	400		
Output Admittance	h_{oe}	3.0	60	S	
Current Gain-Bandwidth Product	f_T	250		MHz	$V_{CE} = -20\text{V}$, $I_C = -10\text{mA}$, $f = 100\text{MHz}$
Noise Figure	NF		4.0	dB	$V_{CE} = -5.0\text{V}$, $I_C = -100\text{ A}$, $R_S = 1.0\text{k}$ $f = 1.0\text{kHz}$
SWITCHING CHARACTERISTICS					
Delay Time	t_d		35	ns	$V_{CC} = -3.0\text{V}$, $I_C = -10\text{mA}$, $V_{BE(off)} = 0.5\text{V}$, $I_{B1} = -1.0\text{mA}$
Rise Time	t_r		35	ns	
Storage Time	t_s		225	ns	$V_{CC} = -3.0\text{V}$, $I_C = -10\text{mA}$, $I_{B1} = I_{B2} = -1.0\text{mA}$
Fall Time	t_f		75	ns	

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